

**Trench™ HiperFET™
Power MOSFET**

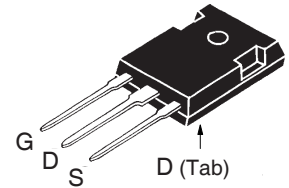
IXFH110N25T

V_{DSS} = 250V
I_{D25} = 110A
R_{DS(on)} ≤ 26mΩ

N-Channel Enhancement Mode
 Avalanche Rated
 Fast Intrinsic Rectifier



TO-247



G = Gate D = Drain
 S = Source Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
V _{DSS}	T _J = 25°C to 150°C	250	V
V _{DGR}	T _J = 25°C to 150°C, R _{GS} = 1MΩ	250	V
V _{GSS}	Continuous	±20	V
V _{GSM}	Transient	±30	V
I _{D25}	T _C = 25°C	110	A
I _{DM}	T _C = 25°C, Pulse Width Limited by T _{JM}	300	A
I _A	T _C = 25°C	25	A
E _{AS}	T _C = 25°C	1	J
P _D	T _C = 25°C	694	W
dv/dt	I _S ≤ I _{DM} , V _{DD} ≤ V _{DSS} , T _J ≤ 150°C	10	V/ns
T _J		-55 to +150	°C
T _{JM}		+150	°C
T _{stg}		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering	300	°C
T _{SOLD}	1.6 mm (0.062in.) from Case for 10s	260	°C
M _d	Mounting Torque	1.13/10	Nm/lb.in.
Weight		6	g

Features

- International Standard Package
- Avalanche Rated
- High Current Handling Capability
- Fast Intrinsic Rectifier
- Low R_{DS(on)}

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- DC-DC Converters
- Battery Chargers
- Switch-Mode and Resonant-Mode Power Supplies
- DC Choppers
- AC Motor Drives
- Uninterruptible Power Supplies

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV _{DSS}	V _{GS} = 0V, I _D = 250μA	250		V
V _{GS(th)}	V _{DS} = V _{GS} , I _D = 3mA	3.0		5.0 V
I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±200 nA
I _{DSS}	V _{DS} = V _{DSS} , V _{GS} = 0V			10 μA
				1 mA
R _{DS(on)}	V _{GS} = 10V, I _D = 0.5 • I _{D25} , Note 1			26 mΩ

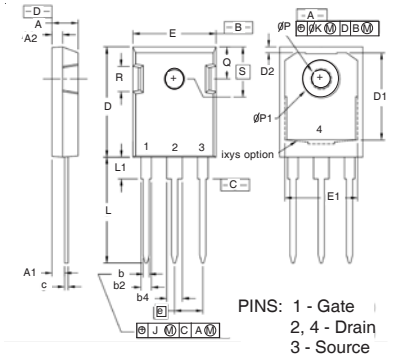
Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 10\text{V}, I_D = 0.5 \cdot I_{D25}$, Note 1	65	110	S
C_{iss}	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		9400	pF
C_{oss}			850	pF
C_{rss}			55	pF
$t_{d(on)}$	Resistive Switching Times $V_{GS} = 15\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		19	ns
t_r			27	ns
$t_{d(off)}$			60	ns
t_f			27	ns
$Q_{g(on)}$		$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 25\text{A}$		157
Q_{gs}			40	nC
Q_{gd}			50	nC
R_{thJC}			0.18	$^\circ\text{C/W}$
R_{thCS}		0.21		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{V}$			110 A
I_{SM}	Repetitive, Pulse Width Limited by T_{JM}			350 A
V_{SD}	$I_F = 55\text{A}, V_{GS} = 0\text{V}$, Note 1			1.2 V
t_{rr}	$I_F = 55\text{A}, -di/dt = 250\text{A}/\mu\text{s},$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			170 ns
I_{RM}			17	A
Q_{RM}			0.95	μC

Note: 1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.

TO-247 (IXFH) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b2	.075	.087	1.91	2.20
b4	.115	.126	2.92	3.20
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
D1	.650	.690	16.51	17.53
D2	.035	.050	0.89	1.27
E	.620	.635	15.75	16.13
E1	.545	.565	13.84	14.35
e	.215 BSC		5.45 BSC	
J	--	.010	--	0.25
K	--	.025	--	0.64
L	.780	.810	19.81	20.57
L1	.150	.170	3.81	4.32
ϕP	.140	.144	3.55	3.65
$\phi P1$.275	.290	6.99	7.37
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.242 BSC		6.15 BSC	

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

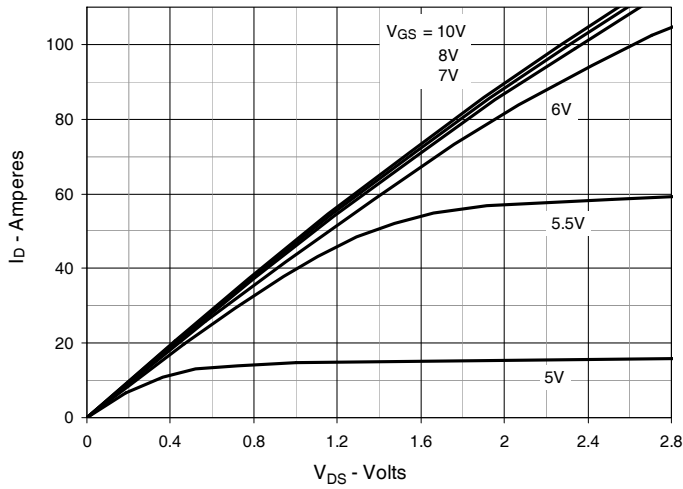


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

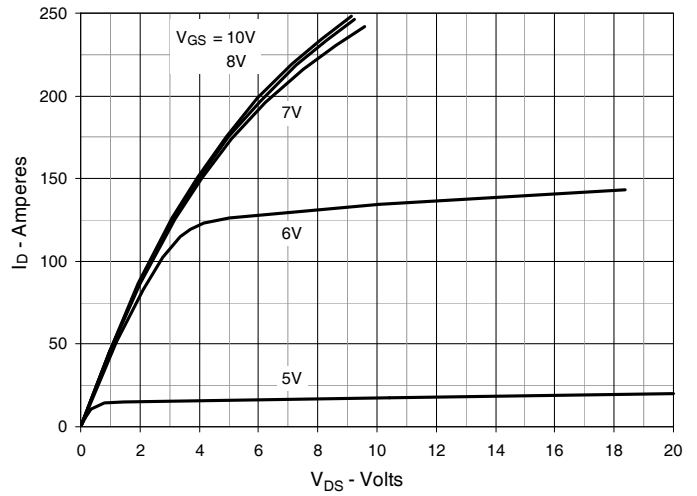


Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

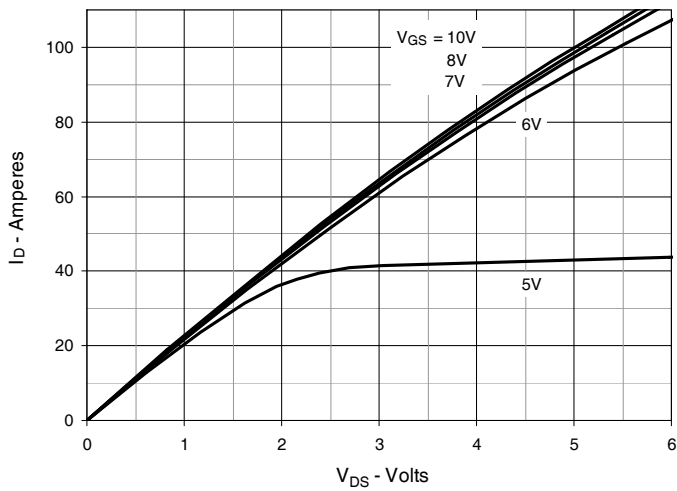


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Junction Temperature

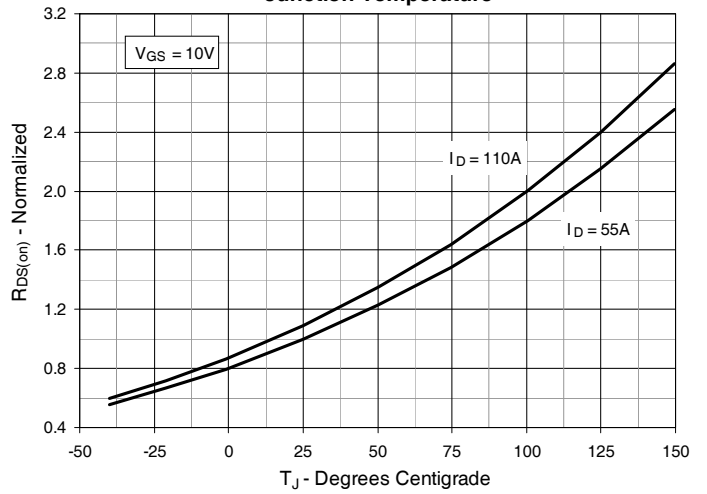


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 55\text{A}$ Value vs. Drain Current

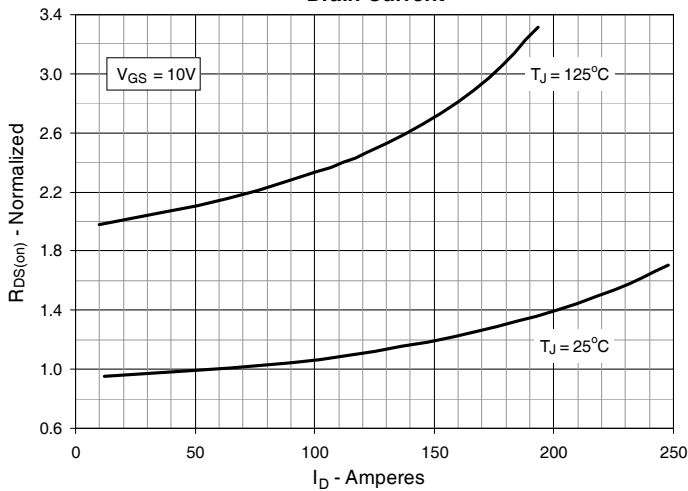


Fig. 6. Drain Current vs. Case Temperature

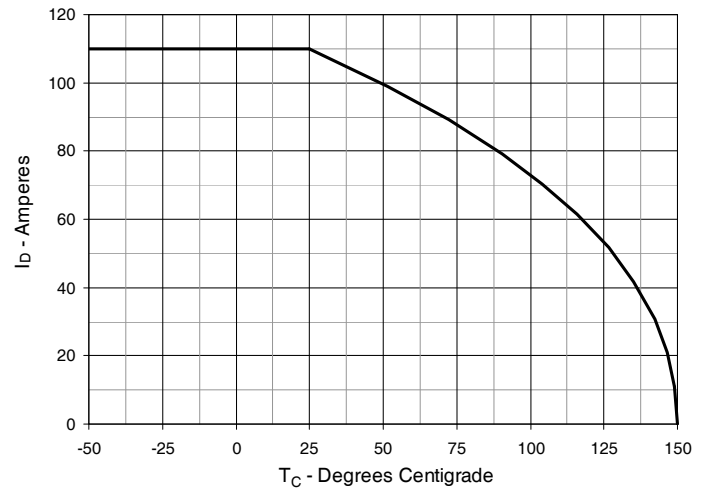


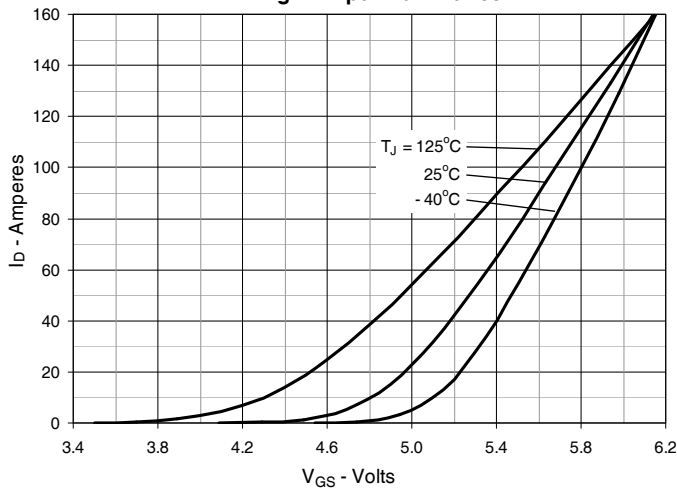
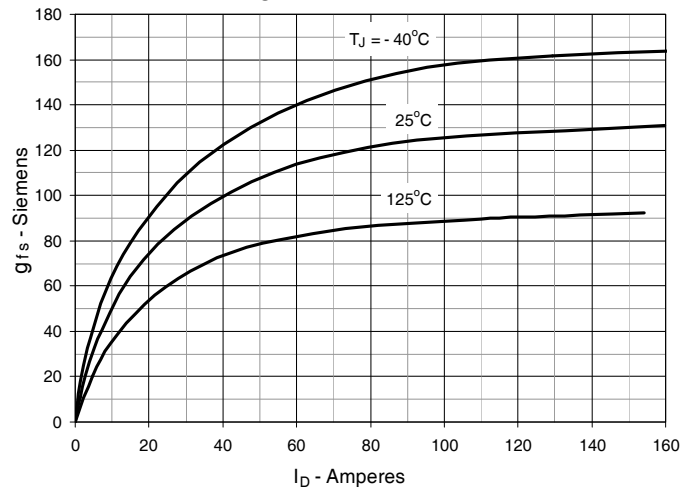
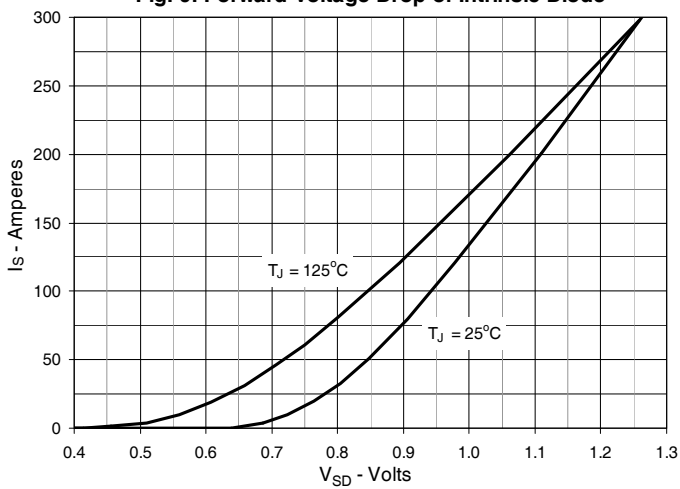
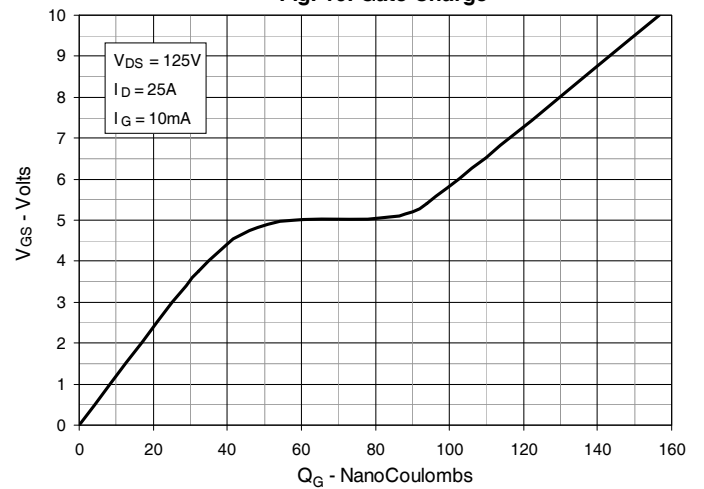
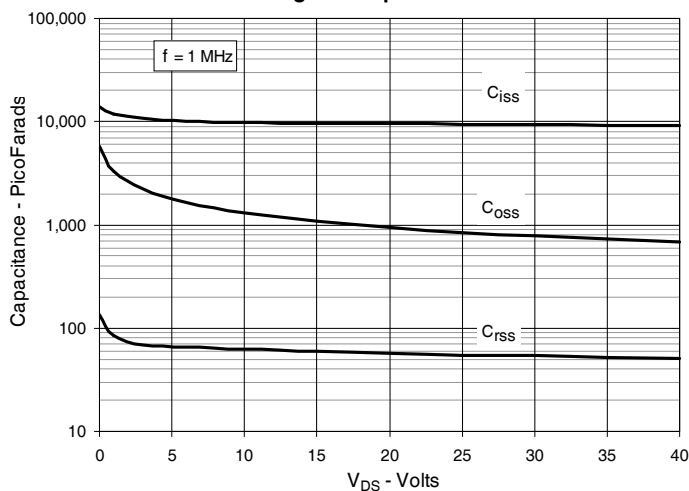
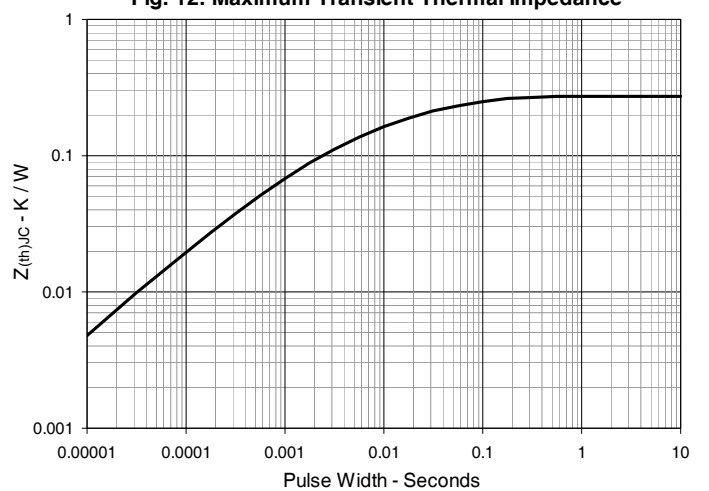
Fig. 7. Input Admittance

Fig. 8. Transconductance

Fig. 9. Forward Voltage Drop of Intrinsic Diode

Fig. 10. Gate Charge

Fig. 11. Capacitance

Fig. 12. Maximum Transient Thermal Impedance


Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature

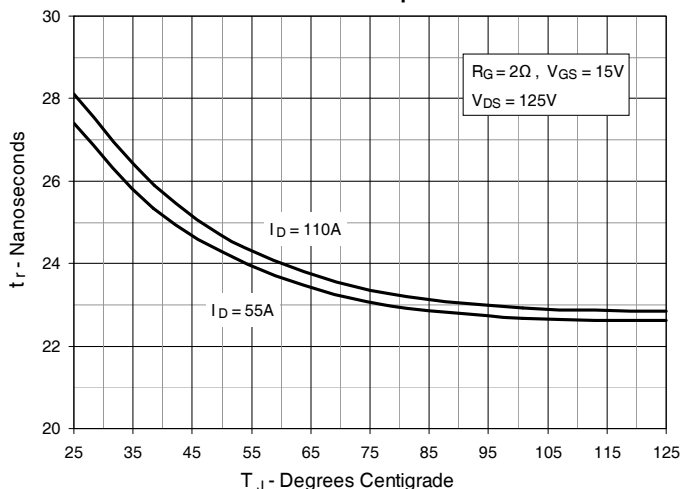


Fig. 14. Resistive Turn-on Rise Time vs. Drain Current

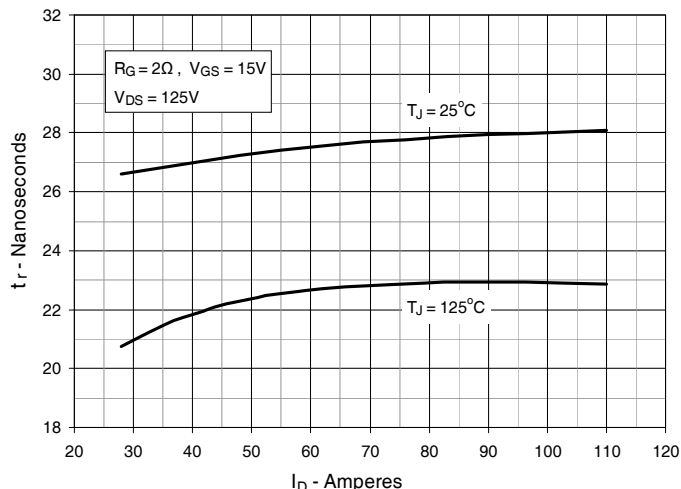


Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance

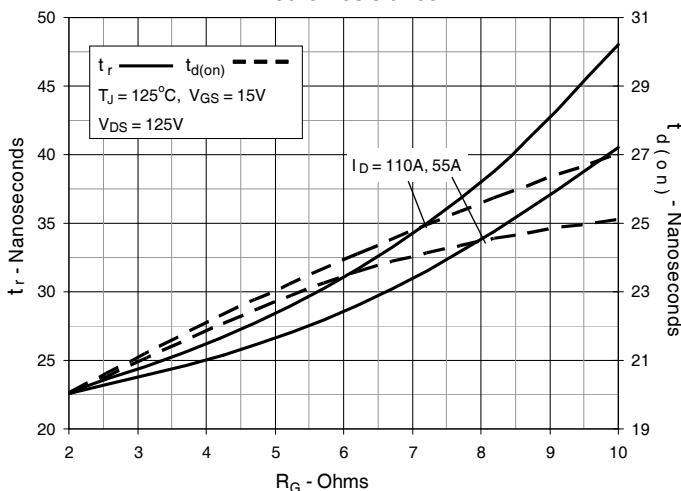


Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature

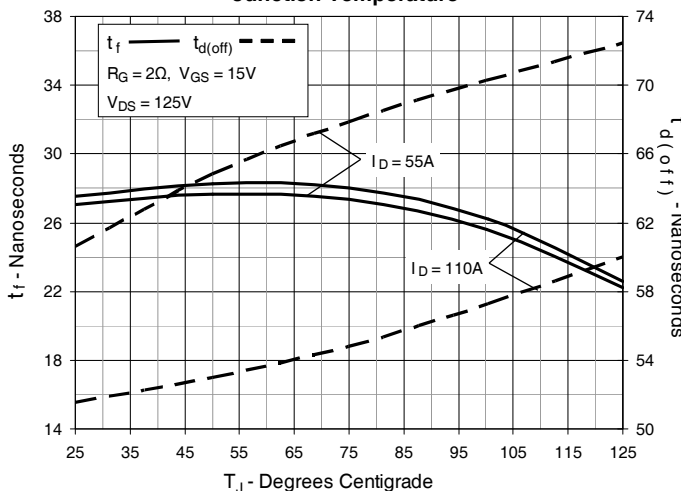


Fig. 17. Resistive Turn-off Switching Times vs. Drain Current

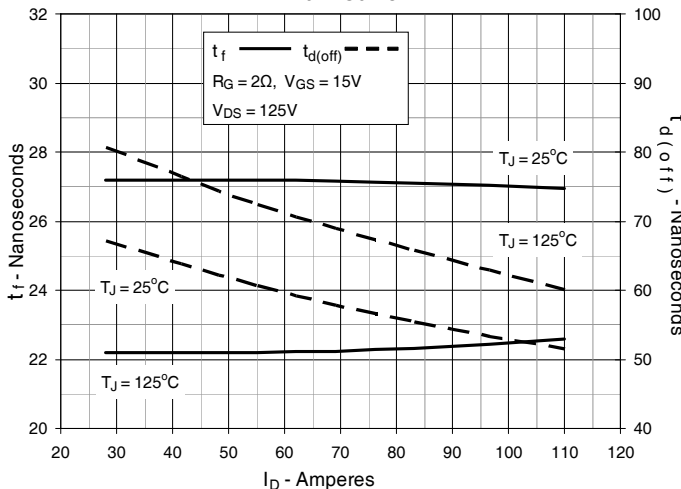


Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance

